

# Andrzej WysmoÅek

## List of Publications by Year in descending order

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165  
papers

2,892  
citations

218381

26  
h-index

189595

50  
g-index

165  
all docs

165  
docs citations

165  
times ranked

3566  
citing authors

#	ARTICLE	IF	CITATIONS
1	Observation of Native Ga Vacancies in GaN by Positron Annihilation. <i>Physical Review Letters</i> , 1997, 79, 3030-3033.	2.9	459
2	Graphene Epitaxy by Chemical Vapor Deposition on SiC. <i>Nano Letters</i> , 2011, 11, 1786-1791.	4.5	296
3	Luminescence and reflectivity in the exciton region of homoepitaxial GaN layers grown on GaN substrates. <i>Solid State Communications</i> , 1996, 97, 919-922.	0.9	130
4	Multiphonon resonant Raman scattering in MoS <sub>2</sub> . <i>Applied Physics Letters</i> , 2014, 104, 092106.	1.5	118
5	Resonant Raman scattering in MoS <sub>2</sub> "From bulk to monolayer. <i>Solid State Communications</i> , 2014, 197, 53-56.	0.9	108
6	Polariton effects in reflectance and emission spectra of homoepitaxial GaN. <i>Physical Review B</i> , 1997, 56, 15151-15156.	1.1	90
7	Quasiclassical cyclotron resonance of Dirac fermions in highly doped graphene. <i>Physical Review B</i> , 2010, 82, .	1.1	86
8	GaN Synthesis by Ammonothermal Method. <i>Acta Physica Polonica A</i> , 1995, 88, 833-836.	0.2	76
9	Raman scattering of few-layers MoTe <sub>2</sub> . <i>2D Materials</i> , 2016, 3, 025010.	2.0	67
10	Recombination of excitons bound to oxygen and silicon donors in freestanding GaN. <i>Physical Review B</i> , 2002, 66, .	1.1	61
11	Transmission electron microscopy and scanning tunneling microscopy investigations of graphene on 4H-SiC(0001). <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	57
12	Carrier Scattering from Dynamical Magnetoconductivity in Quasineutral Epitaxial Graphene. <i>Physical Review Letters</i> , 2011, 107, 216603.	2.9	57
13	Ammonothermal synthesis of GaN doped with transition metal ions (Mn, Fe, Cr). <i>Journal of Alloys and Compounds</i> , 2008, 456, 324-338.	2.8	56
14	Neutral Mn acceptor in bulk GaN in high magnetic fields. <i>Physical Review B</i> , 2004, 70, .	1.1	54
15	Upconverted electroluminescence via Auger scattering of interlayer excitons in van der Waals heterostructures. <i>Nature Communications</i> , 2019, 10, 2335.	5.8	51
16	Symmetry of excitons in GaN. <i>Physical Review B</i> , 1999, 60, 4438-4441.	1.1	45
17	Different paths to tunability in III-V quantum dots. <i>Journal of Applied Physics</i> , 1998, 84, 248-254.	1.1	43
18	Optical Properties of Molybdenum Disulfide (MoS <sub>2</sub> ). <i>Acta Physica Polonica A</i> , 2013, 124, 849-851.	0.2	42

#	ARTICLE	IF	CITATIONS
19	AMMONO method of BN, AlN and GaN synthesis and crystal growth.. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	41
20	Transmission electron microscopy investigations of epitaxial graphene on C-terminated 4H-SiC. Journal of Applied Physics, 2010, 108, .	1.1	35
21	The chemical vapour transport growth of ZnO single crystals. Journal of Alloys and Compounds, 2004, 371, 150-152.	2.8	34
22	Electronic structure of commensurate, nearly commensurate, and incommensurate phases of $S_2T_2$ by angle-resolved photoelectron spectroscopy, scanning tunneling spectroscopy, and density functional theory. Physical Review B, 2018, 98, .	1.1	29
23	Fine optical spectroscopy of the 3.45 eV emission line in GaN nanowires. Journal of Applied Physics, 2013, 113, 043102.	1.1	28
24	Structural and Optical Properties of Homoepitaxial GaN Layers. Materials Research Society Symposia Proceedings, 1996, 449, 393.	0.1	27
25	Micro-Raman spectroscopy of graphene grown on stepped 4H-SiC (0001) surface. Applied Physics Letters, 2012, 100, .	1.5	27
26	Nitrogen doping of chemical vapor deposition grown graphene on 4H-SiC (0001). Journal of Applied Physics, 2014, 115, .	1.1	27
27	The disorder-induced Raman scattering in Au/MoS <sub>2</sub> heterostructures. AIP Advances, 2015, 5, .	0.6	27
28	Growth kinetics of epitaxial graphene on SiC substrates. Physical Review B, 2010, 81, .	1.1	26
29	Fine Structure of Effective Mass Acceptors in Gallium Nitride. Physical Review Letters, 2003, 91, 226404.	2.9	25
30	Dynamics of stacking faults luminescence in GaN/Si nanowires. Journal of Luminescence, 2014, 155, 293-297.	1.5	24
31	Impurity-Related Luminescence of Homoepitaxial GaN Studied with High Magnetic Fields. Physica Status Solidi (B): Basic Research, 1998, 210, 373-383.	0.7	20
32	Photon correlation studies of charge variation in a single GaAlAs quantum dot. Physical Review B, 2013, 87, .	1.1	20
33	Two stage epitaxial growth of wafer-size multilayer h-BN by metal-organic vapor phase epitaxy a homoepitaxial approach. 2D Materials, 2021, 8, 015017.	2.0	20
34	Observation Of Native Ga Vacancies In Gan By Positron Annihilation. Materials Research Society Symposia Proceedings, 1997, 482, 778.	0.1	17
35	Effects of defect scattering on the photoluminescence of exciton-polaritons in n-GaN. Solid State Communications, 1998, 105, 497-501.	0.9	17
36	Resonant interaction of LO phonons with excited donor states in GaN. Physica Status Solidi (B): Basic Research, 2003, 235, 36-39.	0.7	16

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37	Resonant quenching of Raman scattering due to out-of-plane $A_{1g}/A_{2g}^1$ modes in few-layer MoTe <sub>2</sub> . <i>Nanophotonics</i> , 2017, 6, 1281-1288.	2.9	16
38	Growth of Graphene Layers on Silicon Carbide. <i>Materials Science Forum</i> , 0, 615-617, 199-202.	0.3	15
39	Pinned and unpinned epitaxial graphene layers on SiC studied by Raman spectroscopy. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	14
40	Dynamics of thermalization in GaInN/GaN quantum wells grown on ammonothermal GaN. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	14
41	Photoluminescence and Electron Paramagnetic Resonance Studies of Bulk GaN Doped with Gadolinium. <i>Acta Physica Polonica A</i> , 2006, 110, 243-248.	0.2	14
42	Shallow Donors and Acceptors in GaN; Bound Excitons and Pair Spectra. <i>Acta Physica Polonica A</i> , 1996, 90, 681-690.	0.2	14
43	Heteroepitaxial Growth of High Optical Quality, Wafer-Scale van der Waals Heterostructures. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 47904-47911.	4.0	14
44	Spin-orbit splitting of acceptor states in Si and C. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 640-643.	1.3	13
45	Coupled plasmon-LO-phonon modes at high-magnetic fields. <i>Physical Review B</i> , 2006, 74, .	1.1	13
46	Low-strain sensor based on the flexible boron-doped diamond-polymer structures. <i>Carbon</i> , 2021, 173, 832-841.	5.4	13
47	Raman scattering from the bulk inactive out-of-plane $A_{2g}^1$ mode in few-layer MoTe <sub>2</sub> . <i>Scientific Reports</i> , 2018, 8, 17745.	1.6	12
48	Two-Electron Transition in Homoepitaxial GaN Layers. <i>Acta Physica Polonica A</i> , 1997, 92, 742-744.	0.2	12
49	Photoluminescence as a probe of phosphorene properties. <i>Npj 2D Materials and Applications</i> , 2021, 5, .	3.9	11
50	Polarised Magnetoluminescence of Excitons in Homoepitaxial GaN Layers. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 11-15.	0.7	10
51	Emission Due to Exciton Scattering by LO-Phonons in Gallium Nitride. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 95-99.	0.7	10
52	Manganese as a fast charge carrier trapping center in InP. <i>Physica B: Condensed Matter</i> , 2006, 382, 220-228.	1.3	10
53	Raman Optical Activity of 1T-TaS <sub>2</sub> . <i>Nano Letters</i> , 2022, 22, 2835-2842.	4.5	10
54	Enhancement of elastic and inelastic scattering lengths in quasi-free-standing graphene measured with contactless microwave spectroscopy. <i>Physical Review B</i> , 2013, 88, .	1.1	9

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55	Enhanced Raman scattering and weak localization in graphene deposited on GaN nanowires. <i>Physical Review B</i> , 2015, 92, .	1.1	9
56	<i>In situ</i> Raman spectroscopy of the graphene/water interface of a solution-gated field-effect transistor: electron-phonon coupling and spectroelectrochemistry. <i>Nanotechnology</i> , 2016, 27, 045704.	1.3	9
57	Impeded phase transition in 1T-TaS <sub>2</sub> : Thermoelectric fingerprint of long-lived mixed states. <i>Solid State Communications</i> , 2020, 305, 113749.	0.9	9
58	Stable Field Electron Emission and Plasma Illumination from Boron and Nitrogen Co-doped Edge-rich Diamond-enhanced Carbon Nanowalls. <i>Advanced Materials Interfaces</i> , 2021, 8, 2100464.	1.9	9
59	Emission from Mesoscopic-Size Islands Formed in a GaAs/AlAs Double Layer Structure. <i>Acta Physica Polonica A</i> , 2004, 106, 367-381.	0.2	9
60	Enhancement of graphene-related and substrate-related Raman modes through dielectric layer deposition. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	9
61	Interactions of LO Phonons with Bound Excitons in Homoepitaxial GaN. <i>Materials Research Society Symposia Proceedings</i> , 1997, 482, 545.	0.1	8
62	Electrically modulated photoluminescence in self-organized InGaAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 1998, 73, 2811-2813.	1.5	8
63	Single-dot-like emission induced by high magnetic fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 876-879.	1.3	8
64	Low density GaN quantum dots on AlGaIn. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1486-1489.	0.7	8
65	Optical properties of N-polar GaN: The possible role of nitrogen vacancy-related defects. <i>Applied Surface Science</i> , 2021, 566, 150734.	3.1	8
66	Surface-enhanced Raman scattering of graphene caused by self-induced nanogating by GaN nanowire array. <i>Carbon</i> , 2018, 128, 70-77.	5.4	8
67	Reply to "Comment on "Recombination of excitons bound to oxygen and silicon donors in freestanding GaN". <i>Physical Review B</i> , 2004, 69, .	1.1	7
68	Magnetopolaron effect on shallow donors in GaN. <i>Physical Review B</i> , 2006, 74, .	1.1	7
69	Growth Rate and Thickness Uniformity of Epitaxial Graphene. <i>Materials Science Forum</i> , 0, 645-648, 569-572.	0.3	7
70	Surface-enhanced Raman scattering in graphene deposited on Al <sub>1-x</sub> Ga <sub>x</sub> N/GaN axial heterostructure nanowires. <i>Applied Surface Science</i> , 2019, 475, 559-564.	3.1	7
71	Growth and Properties of Bulk Single Crystals of GaN. <i>Materials Research Society Symposia Proceedings</i> , 1995, 395, 15.	0.1	6
72	Growth of low-density GaN quantum dots on Al <sub>x</sub> Ga <sub>1-x</sub> N. <i>Journal of Crystal Growth</i> , 2006, 289, 472-476.	0.7	6

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73	A micro-magneto-Raman scattering study of graphene on a bulk graphite substrate. <i>Europhysics Letters</i> , 2014, 108, 27011.	0.7	6
74	Tuning Light-Driven Water Oxidation Efficiency of Molybdenum-Doped BiVO <sub>4</sub> by Means of Multicomposite Catalysts Containing Nickel, Iron, and Chromium Oxides. <i>ChemPlusChem</i> , 2020, 85, 327-333.	1.3	6
75	Towards practical applications of quantum emitters in boron nitride. <i>Scientific Reports</i> , 2021, 11, 15506.	1.6	6
76	Enhanced Zeeman effect in GGG:Mn <sup>4+</sup> ,Ca crystals. <i>Chemical Physics</i> , 2004, 298, 267-272.	0.9	5
77	Anomalous size effect in thermal residual stresses in pressure sintered alumina-chromium composites. <i>Materials Science &amp; Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2019, 762, 138111.	2.6	5
78	Optical measurements of thermal residual stresses in alumina reinforced with chromium. <i>Journal of Applied Physics</i> , 2019, 125, 135104.	1.1	5
79	Optical Absorption and Raman Scattering Studies of Few-Layer Epitaxial Graphene Grown on 4H-SiC Substrates. <i>Acta Physica Polonica A</i> , 2009, 116, 835-837.	0.2	5
80	Raman Piezospectroscopy of Phonons in Bulk 6H-SiC. <i>Acta Physica Polonica A</i> , 2009, 116, 947-949.	0.2	5
81	Inelastic light scattering on coupled plasmon-LO phonon modes in high magnetic fields. <i>Physica B: Condensed Matter</i> , 2001, 298, 216-220.	1.3	4
82	Dynamics of trapping on donors and relaxation of the B-exciton in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 235, 31-35.	0.7	4
83	Electronic structure of shallow impurities in GaN studied via bound exciton magneto-optics. <i>Physica Status Solidi A</i> , 2004, 201, 181-189.	1.7	4
84	Dynamics of ground and excited states of bound excitons in gallium nitride. <i>Journal of Luminescence</i> , 2005, 112, 30-33.	1.5	4
85	DIRECT BANDGAP QUANTUM DOTS EMBEDDED IN A TYPE-II GaAs/AlAs DOUBLE QUANTUM WELL STRUCTURE. <i>International Journal of Modern Physics B</i> , 2007, 21, 1654-1658.	1.0	4
86	In-situ monitoring of electropolymerization processes at boron-doped diamond electrodes by Mach-Zehnder interferometer. <i>Sensors and Actuators B: Chemical</i> , 2020, 304, 127315.	4.0	4
87	Delamination of Large Area Layers of Hexagonal Boron Nitride Grown by MOVPE. <i>Acta Physica Polonica A</i> , 2021, 139, 457-461.	0.2	4
88	Spatially Resolved Micro-Luminescence from GaN/AlGaIn Quantum Dots. <i>Acta Physica Polonica A</i> , 2004, 105, 517-521.	0.2	4
89	Photoluminescence Study of Bulk GaN Doped with Beryllium. <i>Acta Physica Polonica A</i> , 2005, 108, 705-710.	0.2	4
90	Control of Photon Polarization in GaAs/AlAs Single Quantum Dot Emission. <i>Acta Physica Polonica A</i> , 2007, 112, 461-466.	0.2	4

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91	ZnO and ZnO:Mn crystals obtained with the chemical vapour transport method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 884-887.	0.8	3
92	Coupling of phonons with excitons bound to different donors and acceptors in hexagonal GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1940-1943.	0.8	3
93	Magneto-spectroscopy of donor-bound excitons in GaN. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 441-446.	1.3	3
94	Magneto-optical studies of iron impurity in HVPE GaN. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 458-461.	1.3	3
95	Electron scattering in graphene with adsorbed NaCl nanoparticles. <i>Journal of Applied Physics</i> , 2015, 117, 014308.	1.1	3
96	Laser-controlled field effect in graphene/hexagonal boron nitride heterostructures. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	3
97	X-ray and Raman determination of InAsSb mole fraction for $x < 0.5$ . <i>Journal of Crystal Growth</i> , 2018, 498, 137-139.	0.7	3
98	STS observations of deep defects within laser-illuminated graphene/MOVPE-h-BN heterostructures. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	3
99	Suspended graphene on germanium: selective local etching via laser-induced photocorrosion of germanium. <i>2D Materials</i> , 2021, 8, 035043.	2.0	3
100	Properties of graphene deposited on GaN nanowires: influence of nanowire roughness, self-induced nanogating and defects. <i>Beilstein Journal of Nanotechnology</i> , 2021, 12, 566-577.	1.5	3
101	Highly effective gating of graphene on GaN. <i>Applied Surface Science</i> , 2021, 560, 149939.	3.1	3
102	Formation of Mn-Related Defect Band in InP. <i>Acta Physica Polonica A</i> , 2003, 103, 637-642.	0.2	3
103	Anharmonic Optical Phonon Effects in ZnO Nanocrystals. <i>Acta Physica Polonica A</i> , 2011, 119, 678-680.	0.2	3
104	Structural and Optical Properties of Boron Nitride Grown by MOVPE. <i>Acta Physica Polonica A</i> , 2016, 129, A-129-A-131.	0.2	3
105	Raman Spectroscopy of Shear Modes in a Few-Layer MoS <sub>2</sub> . <i>Acta Physica Polonica A</i> , 2016, 129, A-132-A-134.	0.2	3
106	Strong Photoluminescence Fluctuations in Laser-Thinned Few-Layer WS <sub>2</sub> . <i>Acta Physica Polonica A</i> , 2016, 130, 1176-1178.	0.2	3
107	"Excitonic" and Photoionization Absorption Spectra of Iron in III-V Materials. <i>Acta Physica Polonica A</i> , 1992, 82, 911-913.	0.2	3
108	Competition of Radiation Processes in 6H-SiC Observed by Luminescence. <i>Acta Physica Polonica A</i> , 1995, 87, 437-440.	0.2	3

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109	Luminescence Of A New Material: GaN Grown On NdGaO <sub>3</sub> . Materials Research Society Symposia Proceedings, 1997, 482, 748.	0.1	2
110	Modulation of the Yb <sup>3+</sup> to Er <sup>3+</sup> energy transfer in LiNbO <sub>3</sub> crystals by applying magnetic field. Journal of Alloys and Compounds, 2001, 323-324, 344-347.	2.8	2
111	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. International Journal of Modern Physics B, 2004, 18, 3807-3812.	1.0	2
112	Anomalous behaviour of the photoluminescence from GaN/AlGa <sub>N</sub> quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1010-1013.	0.8	2
113	Importance of catalystâ€™ photoabsorber interface design configuration on the performance of Mo-doped BiVO <sub>4</sub> water splitting photoanodes. Journal of Solid State Electrochemistry, 2021, 25, 173-185.	1.2	2
114	Carriers Diffusion in GaAs/AlAs Type II Quantum Well. Acta Physica Polonica A, 2005, 108, 755-760.	0.2	2
115	Magneto-Luminescence Study of Silicon-Vacancy in 6Hâ€ŠSi. Acta Physica Polonica A, 2006, 110, 437-442.	0.2	2
116	Time-Resolved Studies of Gallium Nitride Doped with Gadolinium. Acta Physica Polonica A, 2008, 114, 1425-1430.	0.2	2
117	Optical and Electrical Measurements of Low-Temperature InAlAs. Acta Physica Polonica A, 1992, 82, 825-828.	0.2	2
118	Selective magneto-luminescence spectroscopy of donoacceptor pairs in n-GaAs. Physica Status Solidi (B): Basic Research, 2003, 235, 48-53.	0.7	1
119	Optical detection of 2DEG in GaN/AlGa <sub>N</sub> structures - High magnetic field studies. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 193-197.	0.8	1
120	1.4 eV - LUMINESCENCE BAND IN 6H-SiC: SYMMETRY OF THE ASSOCIATED DEFECT. International Journal of Modern Physics B, 2009, 23, 3019-3023.	1.0	1
121	MAGNETO-LUMINESCENCE OF GADOLINIUM DOPED GALLIUM NITRIDE. International Journal of Modern Physics B, 2009, 23, 2994-2998.	1.0	1
122	Graphene Based Flow Sensors. Acta Physica Polonica A, 2014, 126, 1209-1212.	0.2	1
123	ESR Spectroscopy of Graphene with Adsorbed NaCl Particles. Acta Physica Polonica A, 2014, 126, 1187-1189.	0.2	1
124	Anomalous Raman Scattering In Few Monolayer MoTe <sub>2</sub> . MRS Advances, 2017, 2, 1539-1544.	0.5	1
125	Absorption and Emission Properties of Light Emitting Diode Structures Containing GaInN/GaN QWs. Acta Physica Polonica A, 2011, 120, 918-920.	0.2	1
126	Light Induced Modification of Graphene Oxide Layers on GaN Basis. Acta Physica Polonica A, 2016, 130, 1169-1171.	0.2	1



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127	Growth of GaN Metalorganic Chemical Vapour Deposition Layers on GaN Single Crystals. Acta Physica Polonica A, 1995, 88, 861-864.	0.2	1
128	Coupling of LO Phonons to Excitons in GaN. Acta Physica Polonica A, 1996, 90, 981-984.	0.2	1
129	Localization Effects in GaN/AlGaIn Quantum Well - Photoluminescence Studies. Acta Physica Polonica A, 2003, 103, 573-578.	0.2	1
130	Temporal Evolution of Multi-Carrier Complexes in Single GaN/AlGaIn Quantum Dots. Acta Physica Polonica A, 2005, 108, 879-884.	0.2	1
131	In Situ Raman Spectroscopy of Solution-Gated Graphene on Copper. Acta Physica Polonica A, 2017, 132, 360-363.	0.2	1
132	Strain control in graphene on GaN nanowires: Towards pseudomagnetic field engineering. Carbon, 2022, 186, 128-140.	5.4	1
133	Large negative persistent photoconductivity of bulk GaAs <sub>1-x</sub> P <sub>x</sub> () single crystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 325-328.	1.7	0
134	Homoepitaxy of GaN - growth, investigations and applications. , 0, , .		0
135	Magneto-Spectroscopy of Two-Electron Transitions in Homoepitaxial GaN.. Materials Research Society Symposia Proceedings, 2001, 693, 739.	0.1	0
136	Recombination dynamics in GaN/AlGaIn low dimensional structures obtained by SiH <sub>4</sub> treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1069-1072.	0.8	0
137	Neutral Mn Acceptor in GaN Studied in High Magnetic Fields. AIP Conference Proceedings, 2005, , .	0.3	0
138	MAGNETOPOLARON EFFECT ON SILICON AND OXYGEN DONORS IN GAN. International Journal of Modern Physics B, 2007, 21, 1486-1490.	1.0	0
139	Diluted Magnetic III-V Semiconductors With Mn For Possible Spintronic Applications. AIP Conference Proceedings, 2007, , .	0.3	0
140	TEM Investigations of Graphene on 4H-SiC(0001). Materials Science Forum, 2009, 615-617, 207-210.	0.3	0
141	Electroreflectance investigations of quantum confined Stark effect in GaN quantum wells. Journal of Physics: Conference Series, 2010, 253, 012009.	0.3	0
142	Optical and Electrical Studies of Graphene Deposited on GaN Nanowires. Acta Physica Polonica A, 2014, 126, 1087-1089.	0.2	0
143	Free Excitonic Emission in Homoepitaxial Layers Grown on Bulk GaN Substrates. Acta Physica Polonica A, 2021, 139, 300-303.	0.2	0
144	Charge Transfer in 1T-TaS <sub>2</sub> /Graphene Hybrid Structures Studied by Spatially Resolved Raman Spectroscopy. Acta Physica Polonica A, 2021, 139, 311-313.	0.2	0

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145	MAGNETO-LUMINESCENCE OF A SINGLE LATERAL ISLAND FORMED IN A TYPE - II GaAs/AlAs QW. , 2005, , .		0
146	Magnetized Plasma in Polar Semiconductors. Acta Physica Polonica A, 2007, 112, 141-152.	0.2	0
147	Single GaN/AlGaIn Quantum Dot Spectroscopy. Acta Physica Polonica A, 2007, 112, 233-236.	0.2	0
148	Magnetoluminescence Studies of GaN:Fe. Acta Physica Polonica A, 2007, 112, 177-182.	0.2	0
149	Time Resolved Magnetophotoluminescence of Biased GaAs/AlGaAs Double Quantum Well Structure. Acta Physica Polonica A, 2008, 114, 1369-1374.	0.2	0
150	Transmission Electron Microscopy and Luminescence Studies of Quantum Well Structures Resulting from Stacking Fault Formation in 4H-SiC Layers. Acta Physica Polonica A, 2008, 114, 1067-1072.	0.2	0
151	Time Evolution of the Microluminescence Energy of GaN/AlGaIn Quantum Dots. Acta Physica Polonica A, 2009, 116, 933-935.	0.2	0
152	Built-In Electric Field in High Quality GaN/AlGaIn Quantum Wells. Acta Physica Polonica A, 2011, 119, 657-659.	0.2	0
153	Raman Studies of Defects in Graphene Grown on SiC. Acta Physica Polonica A, 2011, 119, 595-596.	0.2	0
154	Optical and Electrical Studies of FR1 and FR2 Defects in GaAs. Acta Physica Polonica A, 1992, 82, 613-616.	0.2	0
155	Electrical Properties of an Acceptor-like State of Metastable EL2 in n-type GaAs under Uniaxial Stress. Acta Physica Polonica A, 1992, 82, 908-910.	0.2	0
156	Hydrostatic Pressure Spectroscopy of the Vanadium Luminescence in GaAs. Acta Physica Polonica A, 1992, 82, 837-840.	0.2	0
157	Deep Level Transient Spectroscopy Measurements of an Acceptor-like State of Metastable EL2 in GaAs and GaAsP. Acta Physica Polonica A, 1993, 84, 673-676.	0.2	0
158	Orientation of Metastable EL2 under Uniaxial Stress. Acta Physica Polonica A, 1995, 87, 137-140.	0.2	0
159	Influence of Impact Ionization of Shallow Donors on Luminescence in GaAs. Acta Physica Polonica A, 1995, 87, 261-264.	0.2	0
160	GaN Layers Grown by Reactive Ion Plating. Acta Physica Polonica A, 1995, 88, 1058-1062.	0.2	0
161	Origin of Centres Involved in Blue and Orange Luminescence of 6H-SiC. Acta Physica Polonica A, 1995, 88, 957-960.	0.2	0
162	Optical Properties of Self-Organized InGaAs/GaAs Quantum Dots in Field-Effect Structures. Materials Research Society Symposia Proceedings, 1998, 536, 269.	0.1	0

#	ARTICLE	IF	CITATIONS
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